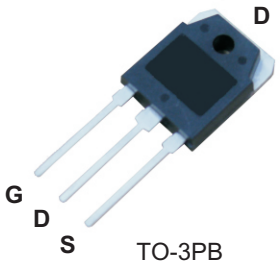
N-Channel Power MOSFET
3.6A, 900Volts

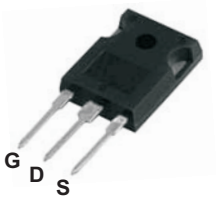
DESCRIPTION

The Nell **IRFF30** is a three-terminal silicon device with current conduction capability of 3.6A, fast switching speed, low on-state resistance, breakdown voltage rating of 900V, and max. threshold voltage of 4 volts.

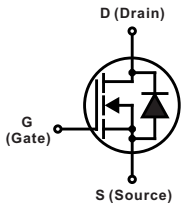
They are designed for use in applications such as switched mode power supplies, DC to DC converters, motor control, circuits UPS and general purpose switching applications.



TO-3PB
(IRFF30B)



TO-247AB
(IRFF30C)



FEATURES

- $R_{DS(ON)}$ = 3.70Ω @ V_{GS} = 10V
- Ultra low gate charge(78nC Max.)
- Low reverse transfer capacitance (C_{RSS} = 200pF typical)
- Fast switching capability
- 100% avalanche energy specified
- Improved dv/dt capability
- 150°C operation temperature

PRODUCT SUMMARY	
I_D (A)	3.6
V_{DSS} (V)	900
$R_{DS(ON)}$ (Ω)	3.70 @ V_{GS} = 10V
Q_G(nC) max.	78

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS	VALUE	UNIT
V_{DSS}	Drain to Source voltage	T_J=25°C to 150°C	900	V
V_{DGR}	Drain to Gate voltage	R_{GS}=20KΩ	900	
V_{GS}	Gate to Source voltage		±20	
I_D	Continuous Drain Current (V_{GS}=10V)	T_C=25°C	3.6	A
		T_C=100°C	2.3	
I_{DM}	Pulsed Drain current(Note 1)		14	
I_{AR}	Avalanche current(Note 1)		3.6	
E_{AR}	Repetitive avalanche energy(Note 1)	I_{AR}=3.6A, R_{GS}=50Ω, V_{GS}=10V	13	mJ
E_{AS}	Single pulse avalanche energy(Note 2)	I_{AS}=3.6A, L=24mH	170	
dv/dt	Peak diode recovery dv/dt(Note 3)		1.5	V /ns
P_D	Total power dissipation	T_C=25°C	125	W
	Derate above 25°C		1.0	W /°C
T_J	Operation junction temperature		-55 to 150	°C
T_{STG}	Storage temperature		-55 to 150	
T_L	Maximum soldering temperature, for 10 seconds	1.6mm from case	300	
	Mounting torque, #6-32 or M3 screw		10 (1.1)	lbf·in (N·m)

Note: 1.Repetitive rating: pulse width limited by junction temperature.
2.I_{AS}=3.6A, L=24mH, V_{DD}=50V, R_G=25Ω, starting T_J=25°C.
3.I_{SD} ≤ 3.6A, di/dt ≤ 70A/μs, V_{DD} ≤ 600V, T_J ≤ 150°C.

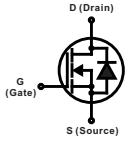
THERMAL RESISTANCE

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
$R_{th(j-c)}$	Thermal resistance, junction to case			1.0	°C/W
$R_{th(c-s)}$	Thermal resistance, case to heat sink		0.24		
$R_{th(j-a)}$	Thermal resistance, junction to ambient			40	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
◎ STATIC							
$V_{(BR)DSS}$	Drain to source breakdown voltage	I_D = 250μA, V_{GS} = 0V		900			V
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown voltage temperature coefficient	I_D = 1mA, V_{DS} = V_{GS}			1.1		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=900V, V_{GS}=0V	T_C = 25°C			100	μA
		V_{DS}=720V, V_{GS}=0V	T_C=125°C			500	
I_{GSS}	Gate to source forward leakage current	V_{GS} = 20V, V_{DS} = 0V				100	nA
	Gate to source reverse leakage current	V_{GS} = -20V, V_{DS} = 0V				-100	
$R_{DS(ON)}$	Static drain to source on-state resistance	I_D = 2.2A, V_{GS} = 10V				3.70	Ω
$V_{GS(TH)}$	Gate threshold voltage	V_{GS}=V_{DS}, I_D=250μA		2.0		4.0	V
g_{fs}	Forward transconductance	V_{DS} = 100V, I_D = 2.2A		2.3			S
◎ DYNAMIC							
C_{ISS}	Input capacitance	V_{DS} = 25V, V_{GS} = 0V, f =1MHz			1200		pF
C_{OSS}	Output capacitance				320		
C_{RSS}	Reverse transfer capacitance				200		
$t_{d(ON)}$	Turn-on delay time	V_{DD} = 450V, V_{GS} = 10V I_D = 3.6A, R_G = 12Ω, R_D = 120Ω (Note1,2)			14		ns
t_r	Rise time				25		
$t_{d(OFF)}$	Turn-off delay time				90		
t_f	Fall time				30		
Q_G	Total gate charge	V_{DD} = 360V, V_{GS} = 10V I_D = 3.6A, (Note1,2)				78	nC
Q_{GS}	Gate to source charge					10	
Q_{GD}	Gate to drain charge (Miller charge)					42	
L_D	Internal drain inductance	Between lead, 6mm(0.25") form package and center of die contact			5		nH
L_S	Internal source inductance				13		

SOURCE TO DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25°C unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{SD}	Diode forward voltage	I_{SD} = 3.6A, V_{GS} = 0V			1.8	V
Is (I_{SD})	Continuous source to drain current	Integral reverse P-N junction diode in the MOSFET			3.6	A
I_{SM}	Pulsed source current				14	
t_{rr}	Reverse recovery time	I_{SD} = 3.6A, V_{GS} = 0V, dI_F/dt = 100A/μs		430	650	ns
Q_{rr}	Reverse recovery charge			1.4	2.1	μC

Note: 1. Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

ORDERING INFORMATION SCHEME

IRF F30 B

MOSFET series

N-Channel,IRF series

Current and Voltage rating, I_D & V_{DS}

3.6A / 900V

Package type

B = TO-3PB

C = TO-247AB

■ TYPICAL CHARACTERISTICS

Fig.1 Typical output characteristics, T_C=25°C

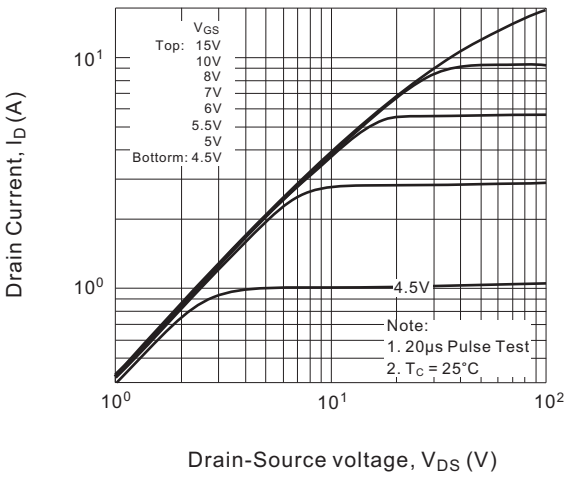


Fig.2 Typical transfer characteristics

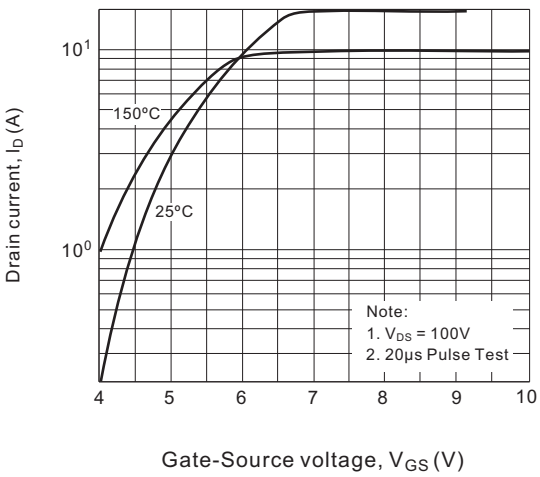


Fig.3 Typical output characteristics, T_C=150°C

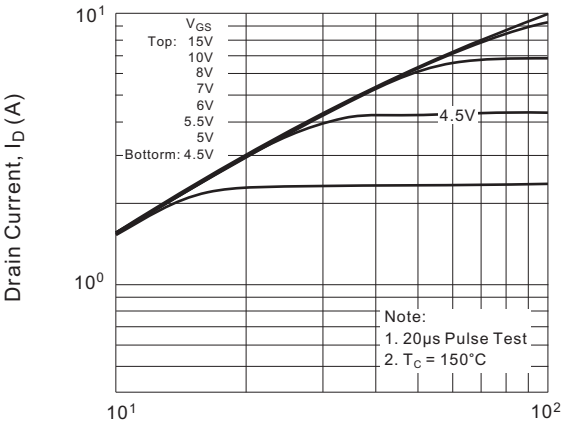


Fig.4 Normalized On-Resistance vs. Temperature

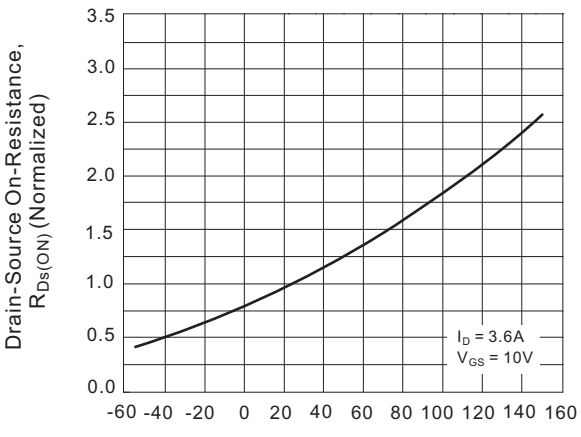


Fig.5 Typical capacitance vs. Drain-to-Source voltage

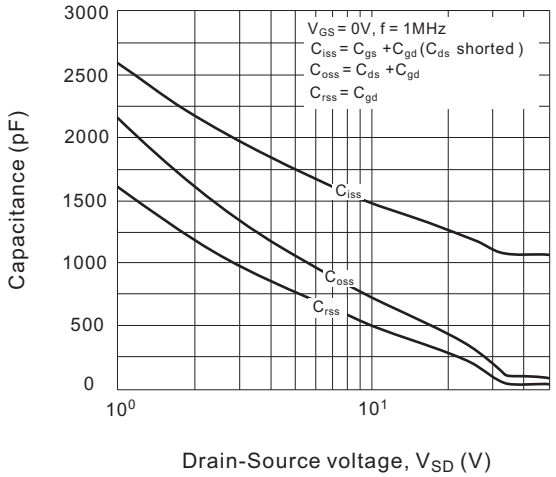


Fig.6 Typical source-drain diode forward voltage

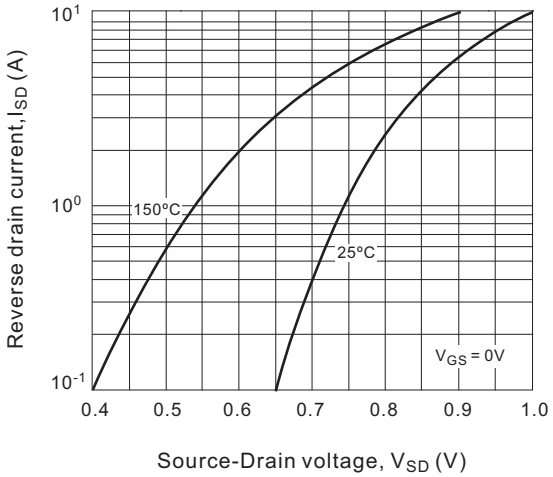


Fig.7 Typical gate charge vs. gate-to-source voltage

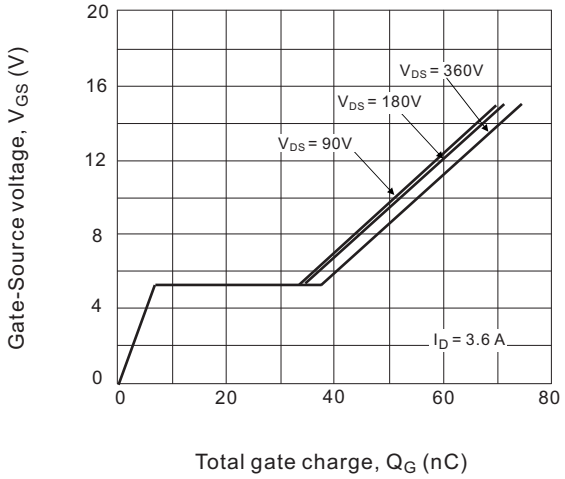


Fig.8 Maximum safe operating area

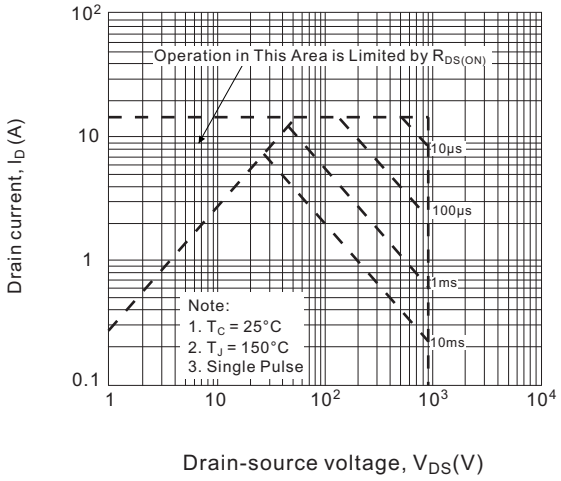


Fig.9 Maximum drain current vs. Case temperature

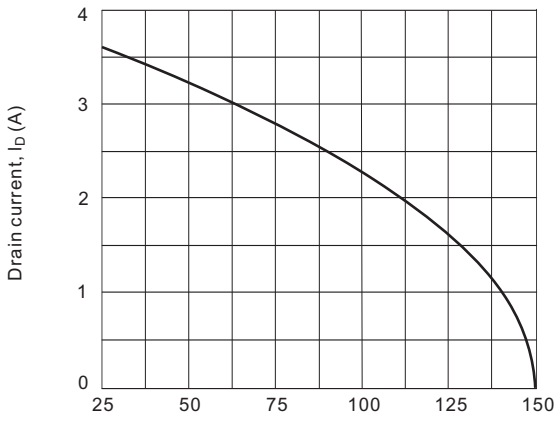


Fig.10 Maximum effective transient thermal impedance, Junction-to-Case

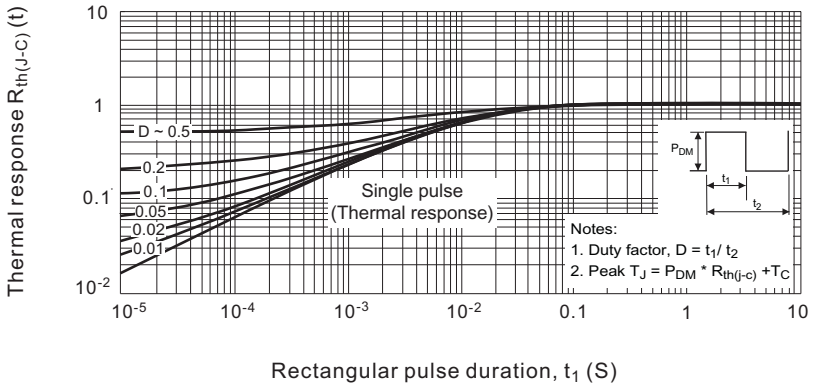


Fig.11a. Switching time test circuit

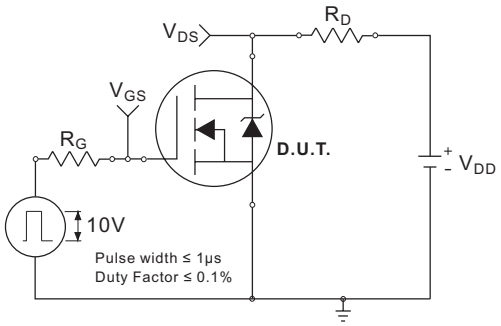


Fig.11b. Switching time waveforms

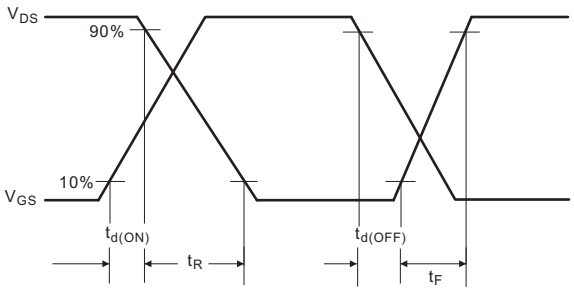
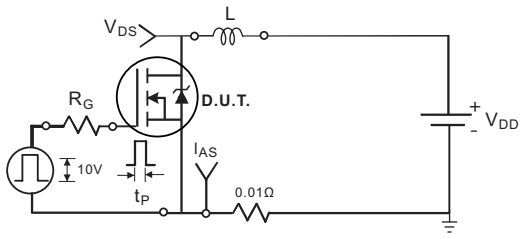


Fig.12a. Unclamped Inductive test circuit



Vary t_p to obtain required I_{AS}

Fig.12b. Unclamped Inductive waveforms

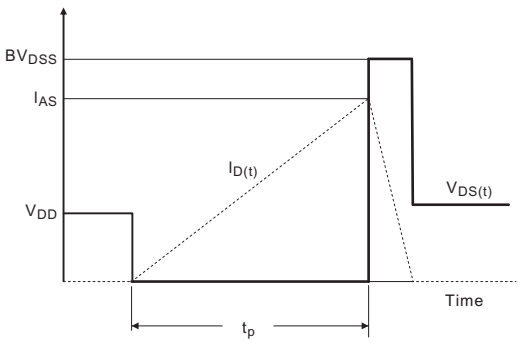


Fig.12c. Maximum avalanche energy vs. Drain current

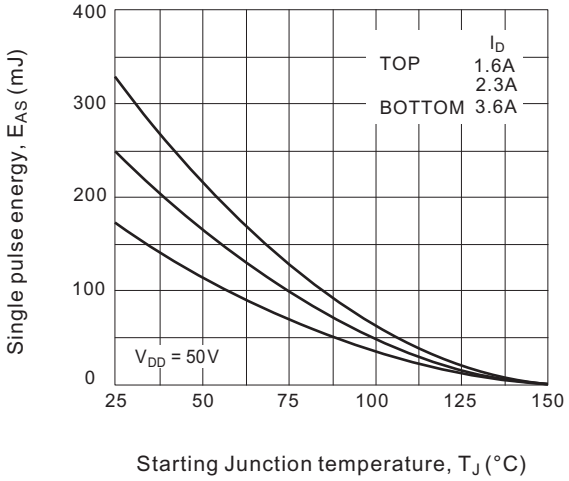


Fig.13a. Basic gate charge waveform

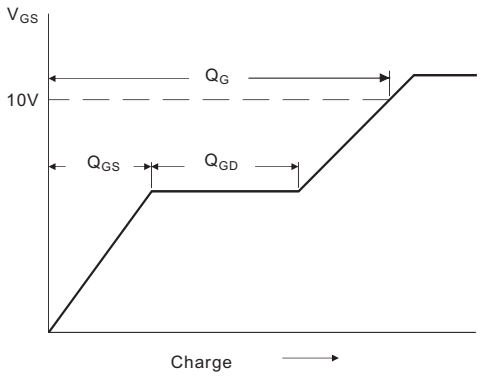


Fig.13b. Gate charge test circuit

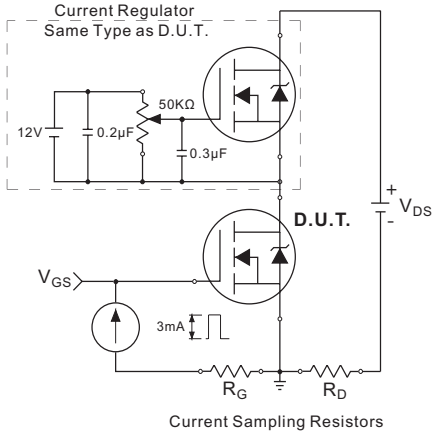
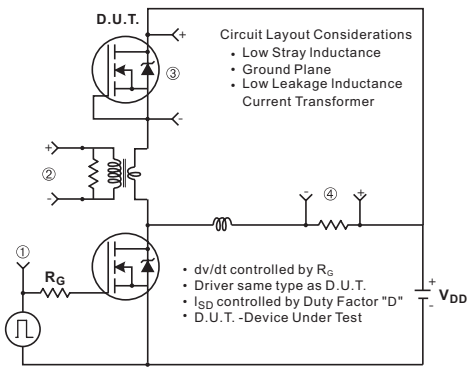
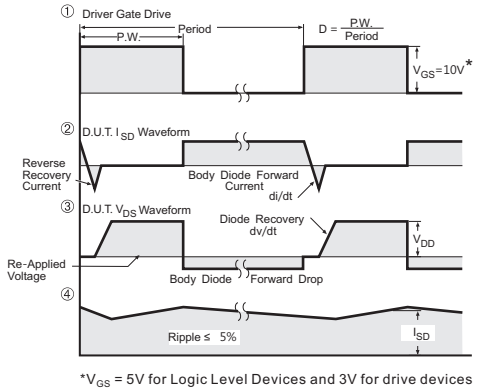


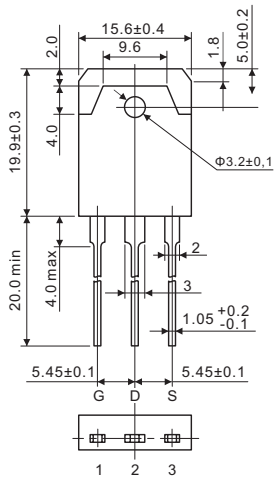
Fig.14 Peak diode recovery dv/dt test circuit for N-Channel MOSFET

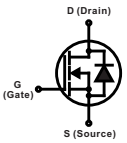




*V_{GS} = 5V for Logic Level Devices and 3V for drive devices

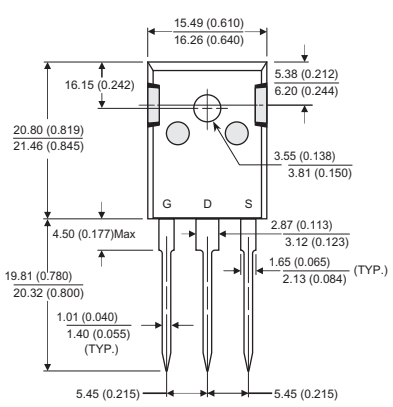
TO-3PB

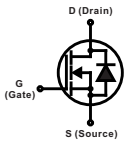




All dimensions in millimeters(inches)

TO-247AB





All dimensions in millimeters(inches)